FQD3P50-VB Datasheet

P-Channel 500V (D-S) Power MOSFET

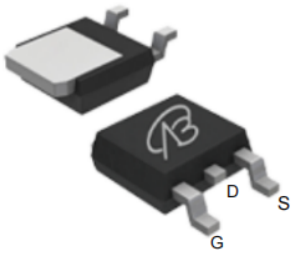
PRODUCT SUMMARY		
V_{DS} (V)	- 500	
$R_{DS(on)}$ (Ω)	V_{GS} = - 10 V	4.0
Q_g (Max.) (nC)	13	
Q_{gs} (nC)	3.2	
Q_{gd} (nC)	5.0	
Configuration	Single	

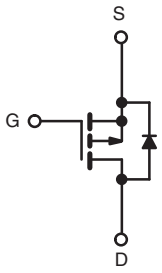
FEATURES

- P-Channel
- Surface Mount
- Straight Lead
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated

RoHS COMPLIANT
HALOGEN FREE Available

DPAK
(TO-252)





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)					
PARAMETER			**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage			V_{DS}	- 500	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at - 10 V	T_C = 25 °C	I_D	- 4.0	A
		T_C = 100 °C		- 3.1	
Pulsed Drain Current[a]			I_{DM}	-15	
Linear Derating Factor				0.40	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	92	mJ
Repetitive Avalanche Current[a]			I_{AR}	- 4	A
Repetitive Avalanche Energy[a]			E_{AR}	15.0	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	80	W
Peak Diode Recovery dV/dt[c]			dV/dt	- 24	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)[d]	for 10 s			300	

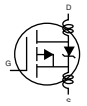
Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Starting T_J = 25 °C, L = 57 mH, R_g = 25 Ω, I_{AS} = - 1.8 A (see fig. 12).
c. I_{SD} ≤ - 1.1 A, dI/dt ≤ 450 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
d. 1.6 mm from case.

THERMAL RESISTANCE RATINGS					
PARAMETER	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	-	110	°C/W
Maximum Junction-to-Ambient (PCB Mount)[a]	R_{thJA}	-	-	50	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	-	2.5	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = - 1 mA	-	- 0.41	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 2.0	-	- 4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 500 V, V_{GS} = 0 V	-	-	- 100	µA
		V_{DS} = - 400 V, V_{GS} = 0 V, T_J = 125 °C	-	-	- 500	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 3.1 A[b]	-	4	-	Ω
Forward Transconductance	g_{fs}	V_{DS} = - 50 V, I_D = - 3.1 A	0.91	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = - 25 V, f = 1.0 MHz, see fig. 5	-	940	-	pF
Output Capacitance	C_{oss}		-	50	-	
Reverse Transfer Capacitance	C_{rss}		-	8.0	-	
Total Gate Charge	Q_g	V_{GS} = - 10 V, I_D = - 1.1 A, V_{DS} = - 320 V, see fig. 6 and 13[b]	-	-	13	nC
Gate-Source Charge	Q_{gs}		-	-	3.2	
Gate-Drain Charge	Q_{gd}		-	-	5.0	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 200 V, I_D = - 1.1 A, R_g = 21 Ω, R_D = 180 Ω, see fig. 10[b]	-	11	-	ns
Rise Time	t_r		-	10	-	
Turn-Off Delay Time	$t_{d(off)}$		-	25	-	
Fall Time	t_f		-	24	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact[c] 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	- 1.9	A
Pulsed Diode Forward Current[a]	I_{SM}		-	-	- 7.6	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = - 1.1 A, V_{GS} = 0 V[b]	-	-	- 4.0	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = -1.1 A, dI/dt = 100 A/µs[b]	-	170	260	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	640	960	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.
c. This is applied for IPAK, L_S of DPAK is measured between lead and center of die contact.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

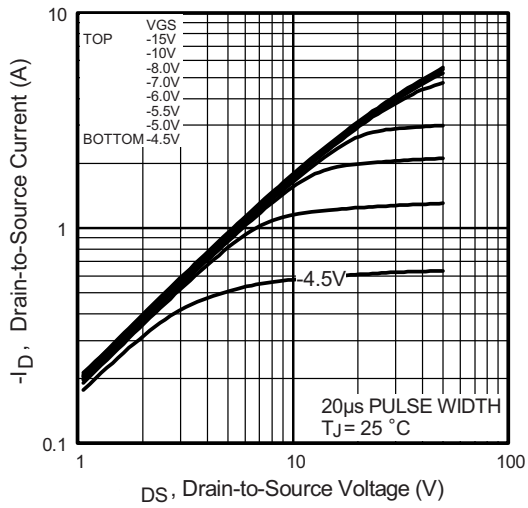


Fig. 1 - Typical Output Characteristics

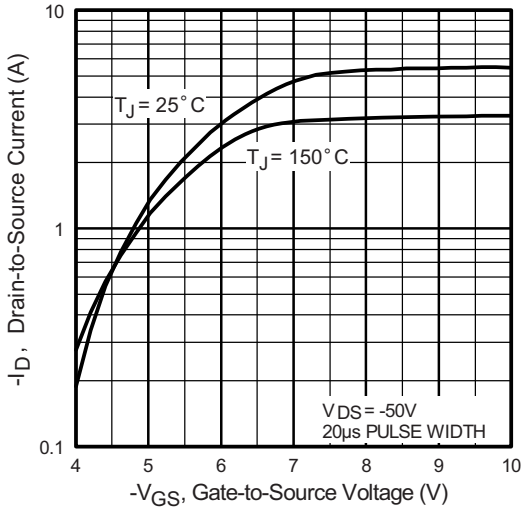


Fig. 3 - Typical Transfer Characteristics

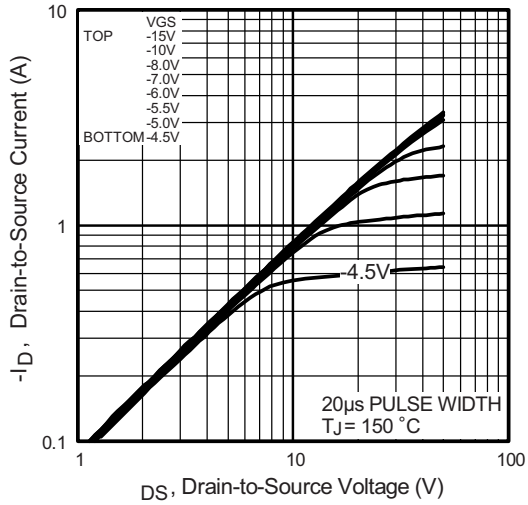


Fig. 2 - Typical Output Characteristics

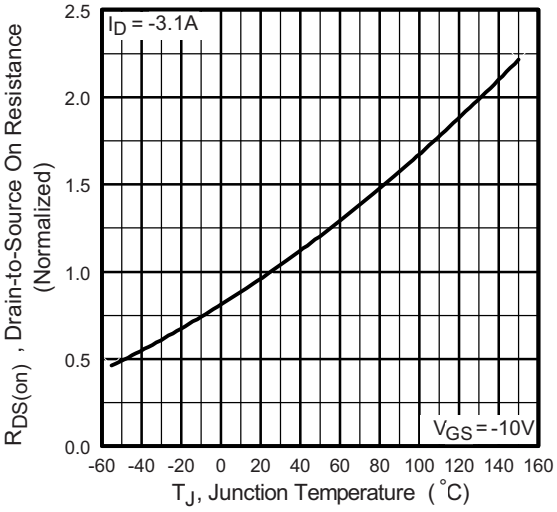


Fig. 4 - Normalized On-Resistance vs. Temperature

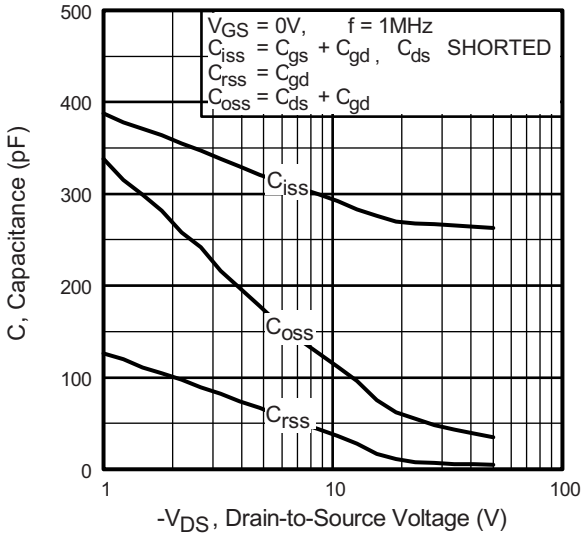


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

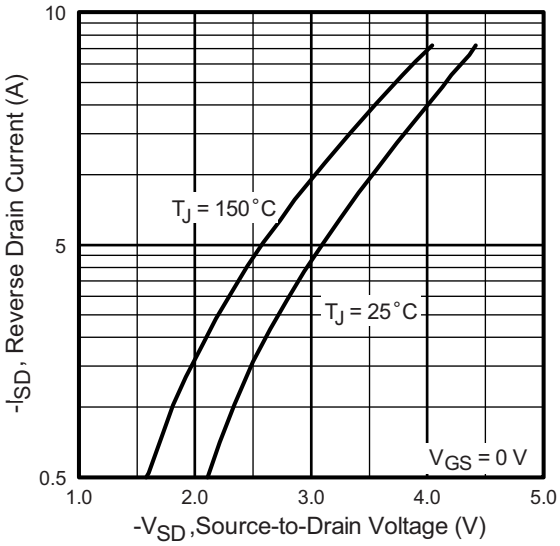


Fig. 7 - Typical Source-Drain Diode Forward Voltage

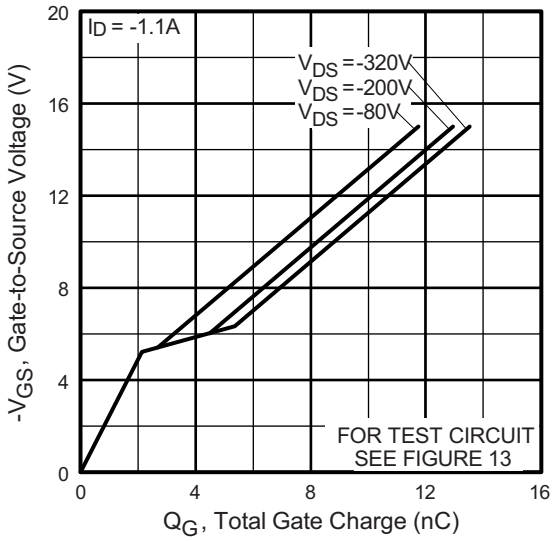


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

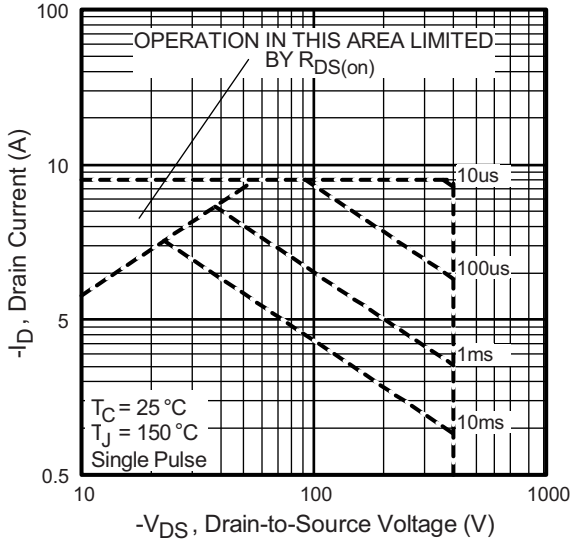


Fig. 8 - Maximum Safe Operating Area

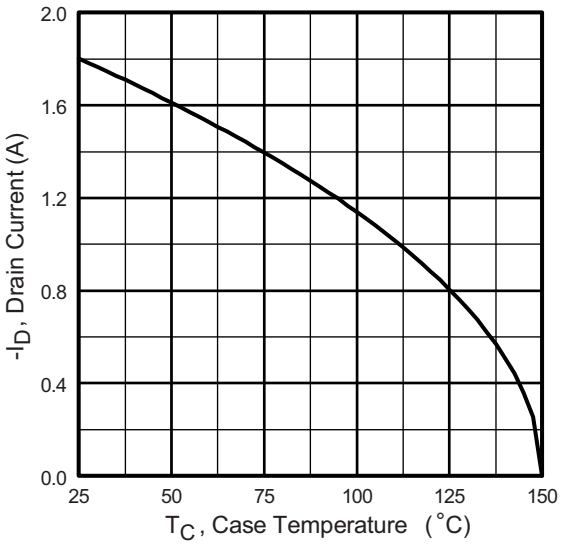


Fig. 9 - Maximum Drain Current vs. Case Temperature

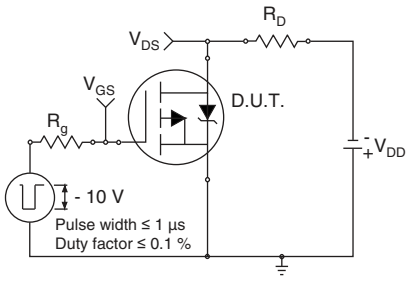


Fig. 10a - Switching Time Test Circuit

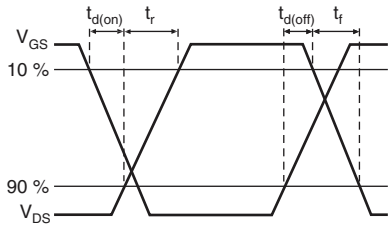


Fig. 10b - Switching Time Waveforms

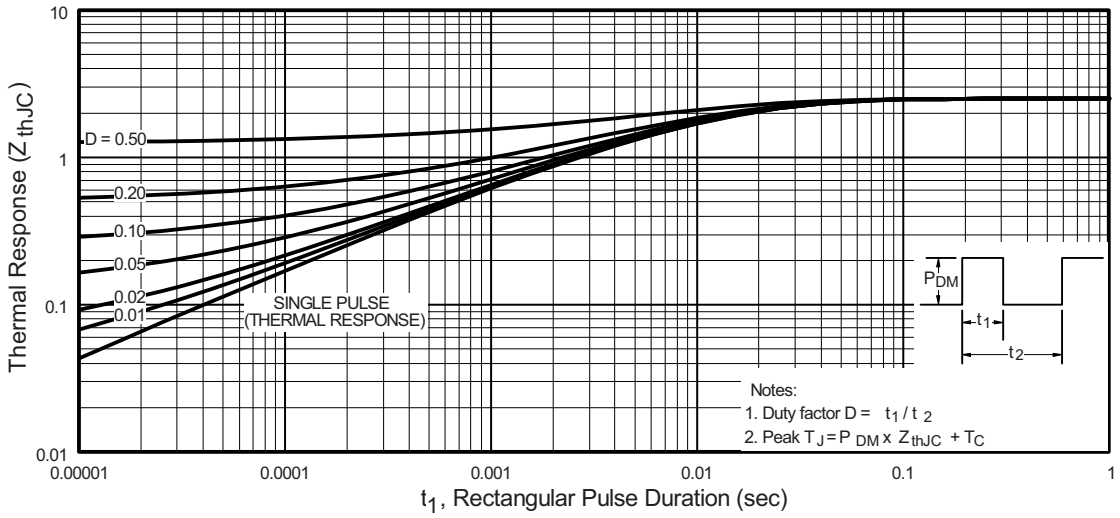


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

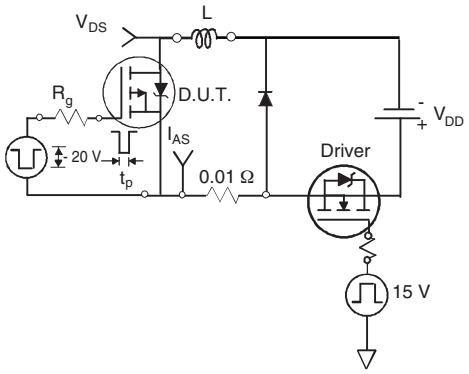


Fig. 12a - Unclamped Inductive Test Circuit

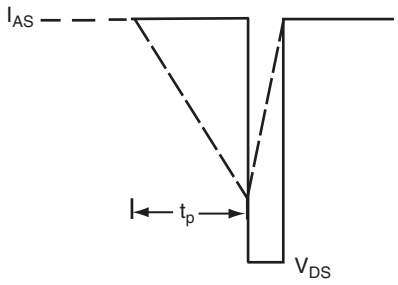


Fig. 12b - Unclamped Inductive Waveforms

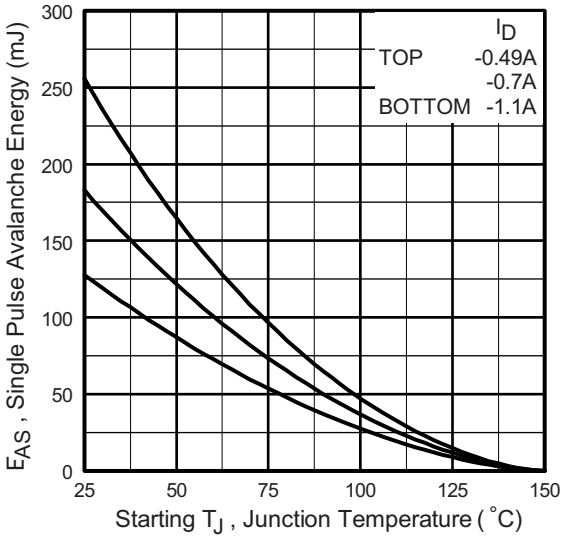


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

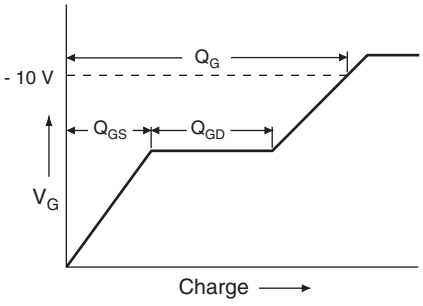


Fig. 13a - Basic Gate Charge Waveform

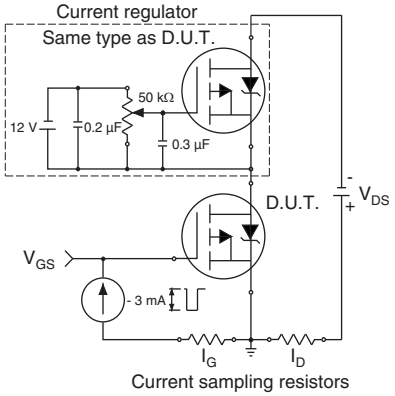
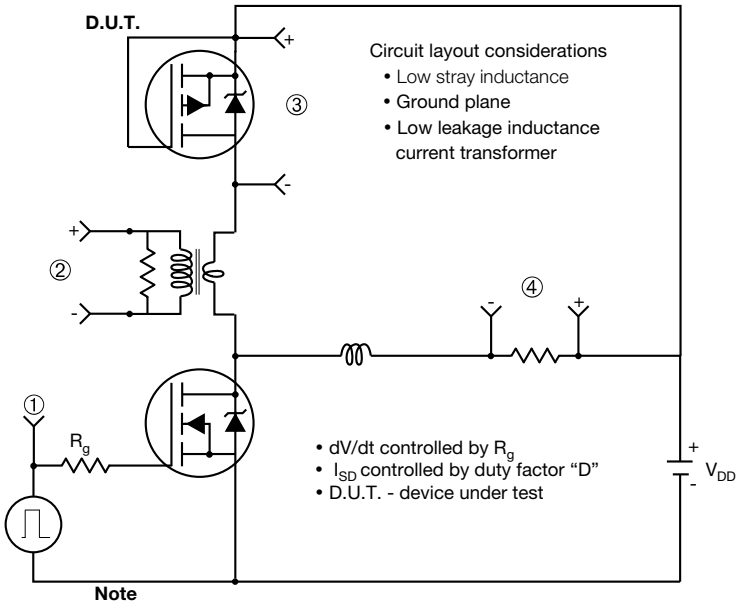
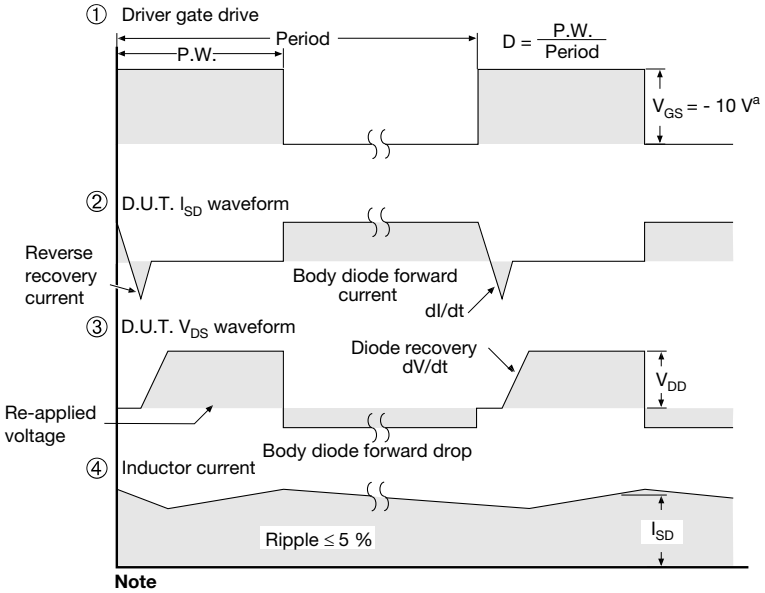


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



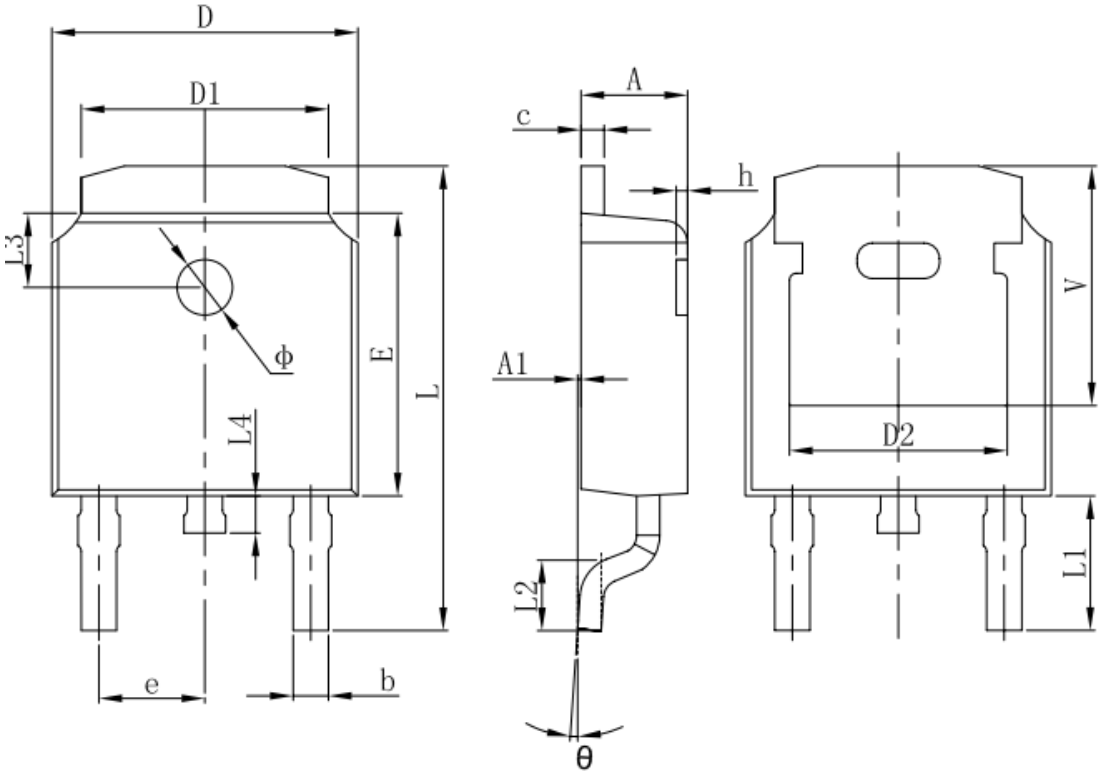
Note
• Compliment N-Channel of D.U.T. for driver



Note
a. V_{GS} = - 5 V for logic level and - 3 V drive devices

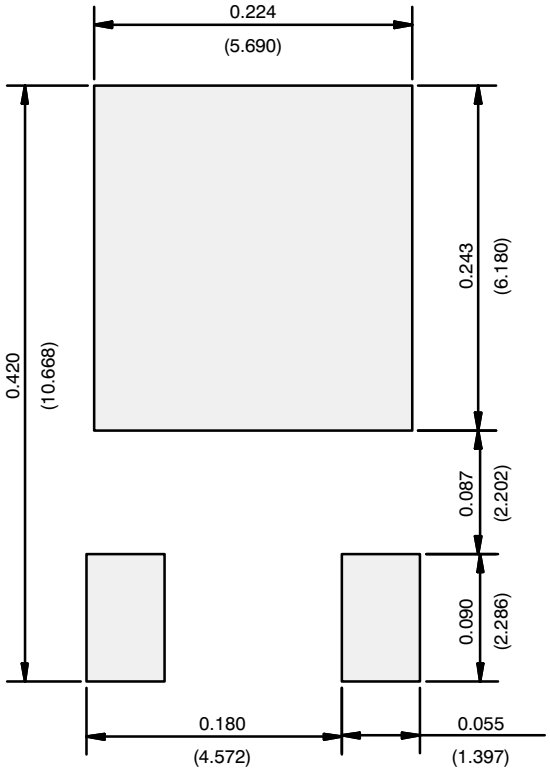
Fig. 14 - For P-Channel

TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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